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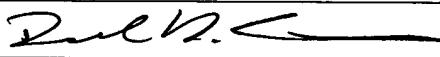
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TRANSMITTAL FORM <i>(to be used for all correspondence after initial filing)</i>		Application Number	10/032,564
		Filing Date	January 2, 2002
		First Named Inventor	Yasutoshi OKUNO et al.
		Group Art Unit	2833
		Examiner Name	M. Estrada
Total Number of Pages in This Submission		Attorney Docket Number	740819-725

ENCLOSURES (check all that apply)				
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Firm or Individual name	Donald R. Studebaker (Reg. No. 32,815) Nixon Peabody LLP 8180 Greensboro Drive Suite 800 McLean, VA 22102
Signature	
Date	August 6, 2002

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#5 Amend A

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

AUG 06 2002 in re Patent Application of

Yasutoshi OKUNO et al.

Serial No. 10/032,564

Filed: January 2, 2002

For: METHOD FOR FABRICATING
SEMICONDUCTOR DEVICE

Group Art Unit: 2823

Examiner: Michelle ESTRADA

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed May 8, 2002, Applicants respectfully submit the following amendments and remarks in connection with the above-captioned matter.

IN THE CLAIMS:

Please amend claims 1 and 3 as follows:

para 51
A 1 1

1. (Amended) A method for fabricating a semiconductor device including a capacitor device having a lower electrode, a capacitor dielectric film formed on said lower electrode and an upper electrode formed on said capacitor dielectric film, comprising a step of:
forming a conducting film to be formed into said lower electrode including sub-steps of:
depositing a lower conducting film on a substrate by sputtering; and
depositing an upper conducting film directly on said lower conducting film by CVD.

para 52
A 2 2

3. (Amended) A method for fabricating a semiconductor device including a capacitor device having a lower electrode, a capacitor dielectric film formed on said lower electrode and an upper electrode formed on said capacitor dielectric film, comprising a step of:
forming a conducting film to be formed into said upper electrode including sub-steps of:
depositing a lower conducting film on said capacitor dielectric film by sputtering; and
depositing an upper conducting film directly on said lower conducting film by CVD.